Silicon NPN Triple Diffused

# HITACHI

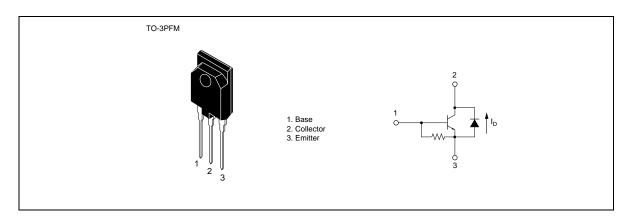
## Application

TV/character display horizontal deflection output

#### Features

- High breakdown voltage V<sub>CES</sub> = 1500 V
- Built-in damper diode type
- Isolated package TO-3PFM

### Outline



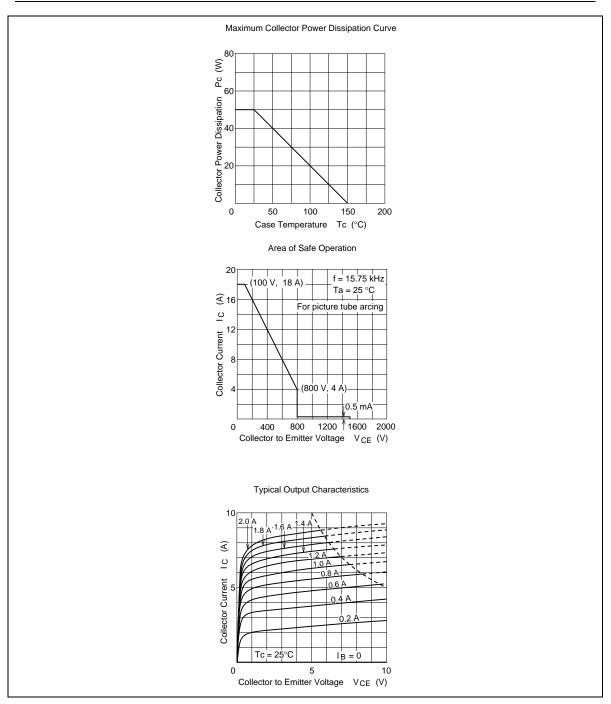
# **Absolute Maximum Ratings** (Ta = 25°C)

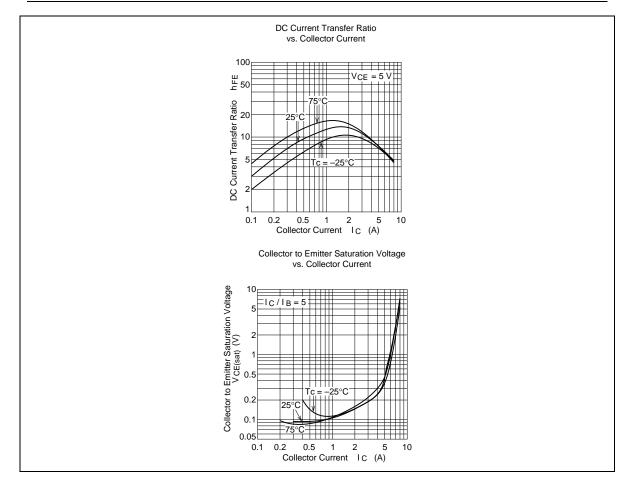
Item	Symbol	Ratings	Unit V	
Collector to emitter voltage	V <sub>ces</sub>	1500		
Emitter to base voltage	V <sub>ebo</sub>	6	V	
Collector current	I <sub>c</sub>	8	А	
Collector peak current	C(peak)	I <sub>C(peak)</sub> 9		
Collector surge current	I <sub>C(surge)</sub>	18	А	
Collector power dissipation	P <sub>c</sub> <sup>*1</sup>	50	W	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55 to +150	°C	
C to E diode forward current	I <sub>D</sub>	8	А	

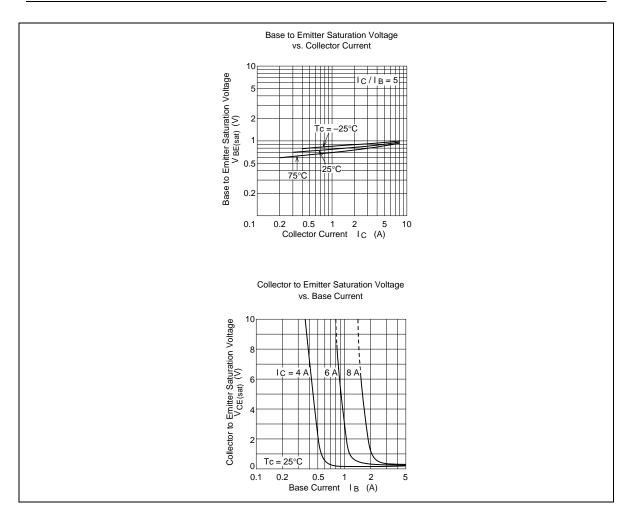
Note: 1. Value at  $T_c = 25^{\circ}C$ .

# **Electrical Characteristics** (Ta = 25°C)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Emitter to base breakdown voltage	$V_{(BR)EBO}$	6	_	_	V	$I_{e} = 500 \text{ mA}, I_{c} = 0$
Collector cutoff current	I <sub>ces</sub>	_	_	500	μA	V <sub>CE</sub> = 1500 V, R <sub>BE</sub> = 0
DC current transfer ratio	$h_{\text{FE}}$	_	_	25	_	$V_{ce} = 5 \text{ V}, I_c = 1 \text{ A}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	—	—	5	V	$I_{c} = 6 \text{ A}, I_{B} = 1.2 \text{ A}$
Base to emitter saturation voltage	$V_{\scriptscriptstyle BE(sat)}$	—	_	1.5	V	$I_{c} = 6 \text{ A}, I_{B} = 1.2 \text{ A}$
C to E diode forward voltage	$V_{ecf}$	_	_	2.0	V	I <sub>F</sub> = 8 A
Fall time	t <sub>r</sub>	—	_	0.5	μs	$I_{_{\rm CP}} = 6$ A, $I_{_{\rm B1}} = 1.2$ A, $I_{_{\rm B2}} \cong -2.4$ A, $f_{_{\rm H}} = 31.5$ kHz







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